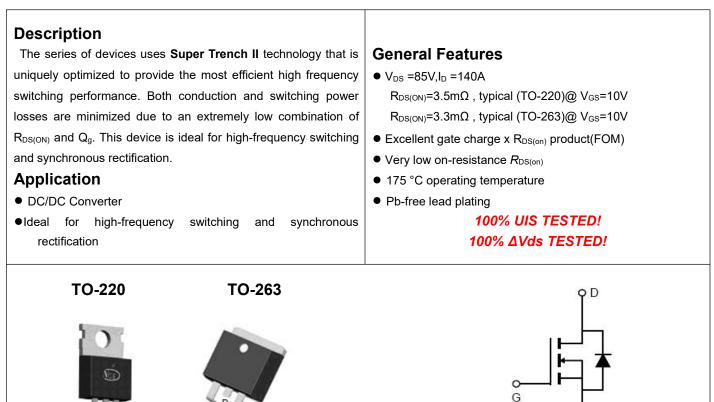


NCE N-Channel Super Trench II Power MOSFET



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP040N85	NCEP040N85	TO-220	-	-	-
NCEP040N85D	NCEP040N85D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	85	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	140	A
Drain Current-Continuous(Tc=100 ℃)	I _D (100℃)	105	A
Pulsed Drain Current	I _{DM}	560	A
Maximum Power Dissipation	PD	200	W
Derating factor		1.33	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	1050	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.75	°C /W
Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{θJA}	60	°C /W

Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Мах	Unit
Off Characteristics	I						1
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS}	s=0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _D	s=0V	-	-	±100	nA
On Characteristics (Note 3)	I						1
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =2	50µA	2.0	3.0	4.0	V
	_		TO-220	-	3.5	4.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =70A	TO-263		3.3	4.0	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =	70A		90	-	S
Dynamic Characteristics (Note4)	I				1		1
Input Capacitance	C _{lss}		0) /	-	4950	-	PF
Output Capacitance	Coss	V _{DS} =40V,V _{GS} =0V, - 4950 - F=1.0MHz - 850 - - 40 -		PF			
Reverse Transfer Capacitance	C _{rss}	F=1.0MH	F=1.0MHz		40	-	PF
Switching Characteristics (Note 4)	I				1		1
Turn-on Delay Time	t _{d(on)}			-	18	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =	70A	-	11	-	nS
Turn-Off Delay Time	t _{d(off)}	$V_{GS}=10V,R_{G}=1.6\Omega$		-	38	-	nS
Turn-Off Fall Time	t _f			-	9	-	nS
Total Gate Charge	Qg		70.4	-	88	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=40V,I_{D}=$		-	22		nC
Gate-Drain Charge	Q _{gd}	– V _{GS} =10V		-	25		nC
Drain-Source Diode Characteristics	I						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =	70A	-		1.2	V
Diode Forward Current (Note 2)	ls			-	-	140	А
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F :	= 70A	-	72	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)		-	102	_	nC

Notes:

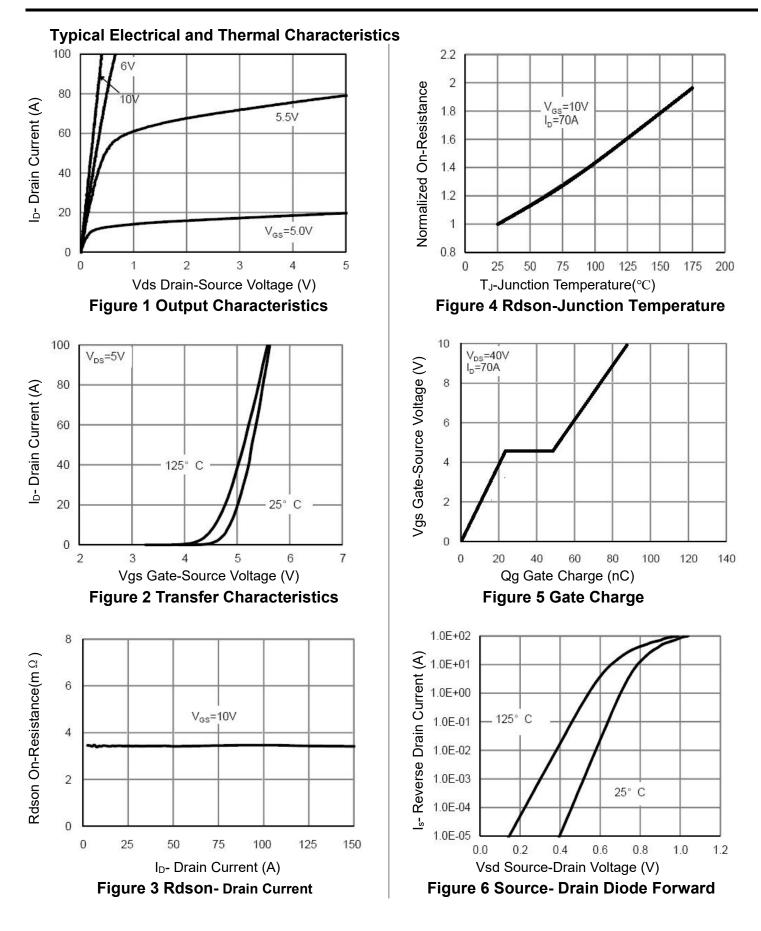
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

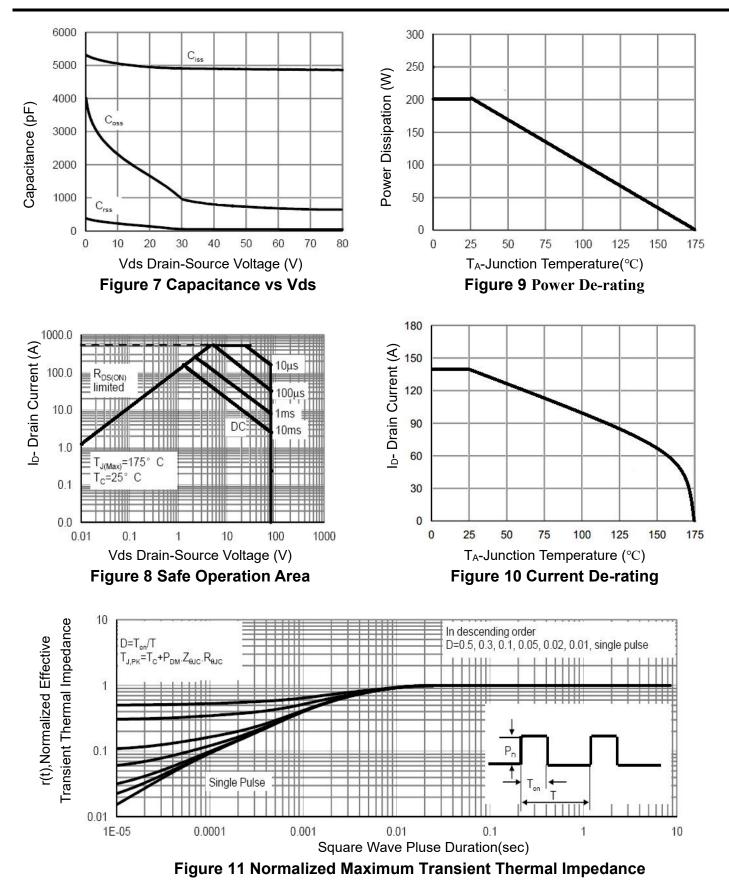
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

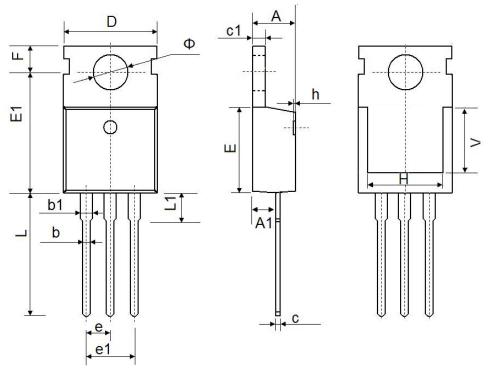
5. EAS condition : Tj=25 $^\circ\!\mathrm{C}$,V_DD=40V,V_G=10V,L=0.5mH,Rg=25 Ω



NCEP040N85, NCEP040N85D

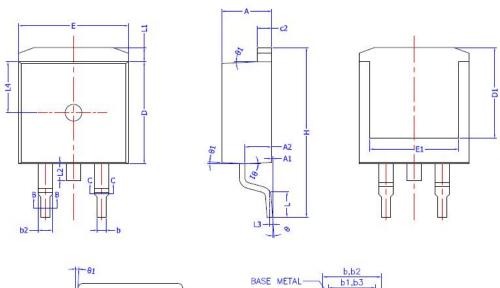


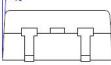
TO-220-3L Package Information

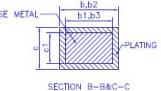


Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Φ	3.400	3.800	0.134	0.150	

TO-263-2L Package Information







COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76		0,89	
b1	0,75	0,80	0,85	
b2	1,23	_	1,37	
b3	1,22	1,27	1,32	
С	0,47	<u> </u>	0,60	
c1	0.46	0,51	0,56	
c2	1.25	1,30	1,35	
D	9.10	9,20	9,30	
D1	8.00	_		
E	9.80	9,90	10.00	
E1	7.80	—	0	
e	2.54 BSC			
Н	14,90	15,30	15,70	
L	2.00	2,30	2,60	
L1	1.17	1.27	1.40	
L2	<u> </u>		1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	_	8°	
θ1	1°	3°	5°	

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